

UT12N10 Preliminary Power MOSFET

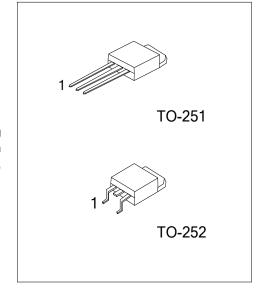
# 12 Amps, 100 Volts N-CHANNEL POWER MOSFET

#### ■ DESCRIPTION

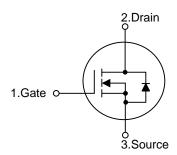
The UTC **UT12N10** is an N-channel mode Power FET using UTC's advanced technology to provide custumers with minimum on-state resistance by extremely high dense cell design. Moreover, it's good at handing high power and current.

#### ■ FEATURES

- \* 100V, 12A,  $R_{DS(ON)} = 180 m\Omega$  @ $V_{GS} = 10V$ .
- \* Be good at handing high power and current.
- \* Very high dense cell design for super low R<sub>DS(ON)</sub>.
- \* Lead free product is acquired.



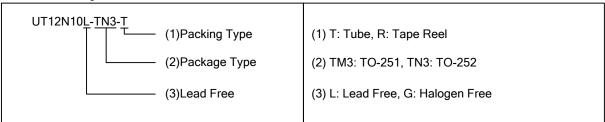
#### ■ SYMBOL



### ■ ORDERING INFORMATION

Ordering Number		Doolsogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UT12N10L-TM3-T	UT12N10G-TM3-T	TO-251	G	D	S	Tube	
UT12N10L-TN3-T	UT12N10G-TN3-T	TO-252	G	D	S	Tube	
UT12N10L-TN3-R	UT12N10G-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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## ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	100	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Drain Current	Continuous	$I_D$	12	Α
	Pulsed (Note 1)	I <sub>DM</sub>	44	Α
Power Dissipation		$P_{D}$	43	W/°C
Junction Temperature		TJ	+150	°C
Storage Temperature		T <sub>STG</sub>	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Note:1 Repetitive Rating: Pulse width limited by maximum junction temperature

## ■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient (Note 2)	$\theta_{JA}$	50	°C/W	
Junction to Case	θ <sub>JC</sub>	3.5	°C/W	

Note:  $\theta_{JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.

 $\theta_{\text{JC}}$  is guaranteed by design while  $\theta_{\text{JA}}$  is determined by the user's board design.

Note: 2 When mounted on a 1 in<sup>2</sup> pad of 2 oz copper

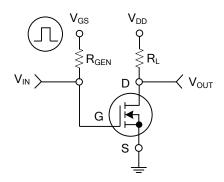
### ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER		SYMBOL	TEST CONDITIONS MIN		TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltag	е	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V				V	
Drain-Source Leakage Current		$I_{DSS}$	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V			1	μΑ	
Gate- Source Leakage Current	Forward		$V_{GS}$ =+20V, $V_{DS}$ =0V			+100	nΑ	
	Reverse	I <sub>GSS</sub>	$V_{GS}$ =-20V, $V_{DS}$ =0V			-100	nΑ	
ON CHARACTERISTICS (Note 1)								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$			4	V	
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A		150	180	mΩ	
Forward Transconductance		<b>g</b> fs	$V_{DS}$ =10V, $I_{D}$ =6A		5		S	
<b>DYNAMIC PARAMETERS</b> (Note	e 2)							
Input Capacitance	nput Capacitance				430		pF	
Output Capacitance		C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz		90		pF	
Reverse Transfer Capacitance		$C_{RSS}$			20		pF	
<b>SWITCHING PARAMETERS</b> (N	ote 2)							
Total Gate Charge		$Q_G$			8	16	nC	
Gate to Source Charge		$Q_GS$	V <sub>GS</sub> =10V, V <sub>DS</sub> =80V, I <sub>D</sub> =12A		1.5		nC	
Gate to Drain Charge		$Q_GD$			2		nC	
Turn-ON Delay Time		t <sub>D(ON)</sub>	$V_{DD}$ =80V, $I_{D}$ =12A, $V_{GS}$ =10V, $R_{G}$ =9.1 $\Omega$		12	24	ns	
Rise Time		$t_R$			7	14	ns	
Turn-OFF Delay Time		t <sub>D(OFF)</sub>			18	35	ns	
Fall-Time		t <sub>F</sub>			3	6	ns	
SOURCE- DRAIN DIODE RATII	NGS AND C	CHARACTERI	STICS					
Maximum Body-Diode Continuous Current		Is				12	Α	
Drain-Source Diode Forward Voltage (Note 1)		$V_{SD}$	I <sub>S</sub> =12A, V <sub>GS</sub> =0V			1.2	V	

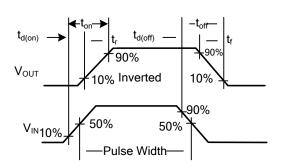
Note: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%

2. Guaranteed by design, not subject to production testing.

## ■ TEST CIRCUITS AND WAVEFORMS



Switching Test Circuit



**Switching Waveforms** 

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